

IN THE CLAIMS:

The following is a complete listing of claims in this application.

Please examine claims 1-14 attached to the International Preliminary Report on Patentability.

1. (original) A substrate (10) designed to support an object (12) for processing, such as a substrate for a semiconductor element, the substrate containing carbon and being equipped with gas outlet or passage openings that intersperse the substrate, characterized in that the substrate (10) is porous, that the porosity of the substrate forms the gas outlet or passage openings, that the substrate is comprised of a framework or a segment of a framework made of carbon fibers and/or SiC fibers (18, 20), that the fibers are embedded in a matrix made of carbon and/or SiC, and that the porosity level p of the substrate is $5\% \leq p \leq 95\%$ and the density ρ of the substrate is $0.1 \text{ g/cm}^3 \leq \rho \leq 3.0 \text{ g/cm}^3$.

2. (original) A substrate according to Claim 1, characterized in that the framework is comprised of carbon felt, non-woven material and/or fabric layers.

3. (original) A substrate according to Claim 1, characterized in that the fibers (18, 20) are provided with one or more carbon or pyrocarbon and/or silicon carbide layers (26, 28) as the matrix.

4. (currently amended) A substrate according to ~~at least one of the preceding claims~~ claim 1, characterized in that the matrix is equipped on its outer surface with a silicon carbide layer.

5. (currently amended) A substrate according to ~~at least one of the preceding claims~~ claim 1, characterized in that the matrix comprises a coating system that transitions in a graduated fashion from carbon to silicon carbide.

6. (currently amended) A substrate according to ~~at least one of the preceding claims~~ claim 1, characterized in that the thermal conductivity w of the substrate (10) ranges from $0.10 \text{ W/mK} \leq w \leq 100 \text{ W/mK}$, especially $3 \text{ W/mK} \leq w \leq 30 \text{ W/mK}$.

7. (currently amended) A substrate according to ~~at least one of the preceding claims~~ claim 1, characterized in that the substrate has a total density of 1.50 g/cm^3 to 1.9 g/cm^3 , the proportion of fibers being 0.098 g/cm^3 to 0.2 g/cm^3 and/or the proportion of pyrocarbon being 0.4 g/cm^3 to 0.8 g/cm^3 and/or the proportion of SiC being 0.8 g/cm^3 to 1.0 g/cm^3 .

8. (currently amended) A substrate according to ~~at least one of the preceding claims~~ claim 1, characterized in that the weight ratio of framework to matrix totals approximately 1:13 to 1:17.

9. (original) A method for producing a substrate designed to support an object for processing, preferably a substrate for a semiconductor element such as a wafer, wherein carbon is used as the material for the substrate, and gas outlet or passage openings are formed, interspersed through the substrate, characterized by the following process steps:

production of a framework made of carbon and/or SiC fibers and

stabilization of the framework with at least one pyrocarbon and/or silicon carbide coating that forms a matrix, such that the stabilized framework has a porosity level that forms the gas outlet or passage openings,

a framework stabilized in this manner, or a segment of the framework, being used as the substrate.

10. (original) A method according to claim 9, characterized in that the fibers are stabilized by means of vapor infiltration (CVI) and/or fluid impregnation.

11 (currently amended) A method according to claim 9 or

10, characterized in that stabilized felt or non-woven materials, or stabilized fabric layers are used as the framework.

12. (currently amended) A method according to ~~at least one of claims 9 through 11~~ claim 9, characterized in that the fibers are stabilized exclusively with carbon or exclusively with silicon carbide.

13. (currently amended) A method according to ~~at least one of claims 9 through 12~~ claim 9, characterized in that the fibers are stabilized with a series of one or more coatings made of carbon and/or silicon carbide.

14. (currently amended) A method according to ~~at least one of claims 9 through 13~~ claim 9, characterized in that the fibers are stabilized with a graduated system of coatings that transitions from carbon to silicon carbide.